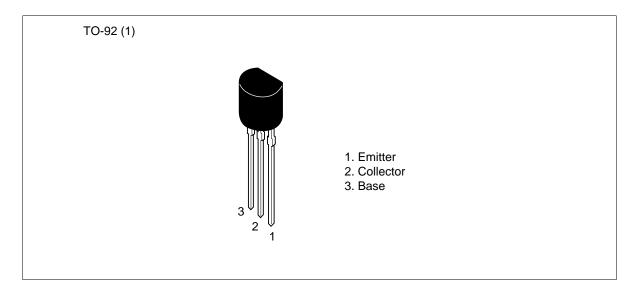
Silicon PNP Epitaxial

HITACHI

Application

- Low frequency low noise amplifier
- Complementary pair with 2SC2855 and 2SC2856

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	2SA1190	2SA1191	Unit
Collector to base voltage	V_{CBO}	-90	-120	V
Collector to emitter voltage	V_{CEO}	-90	-120	V
Emitter to base voltage	V_{EBO}	- 5	- 5	V
Collector current	I _c	-100	-100	mA
Emitter current	I _E	100	100	mA
Collector power dissipation	P _c	400	400	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

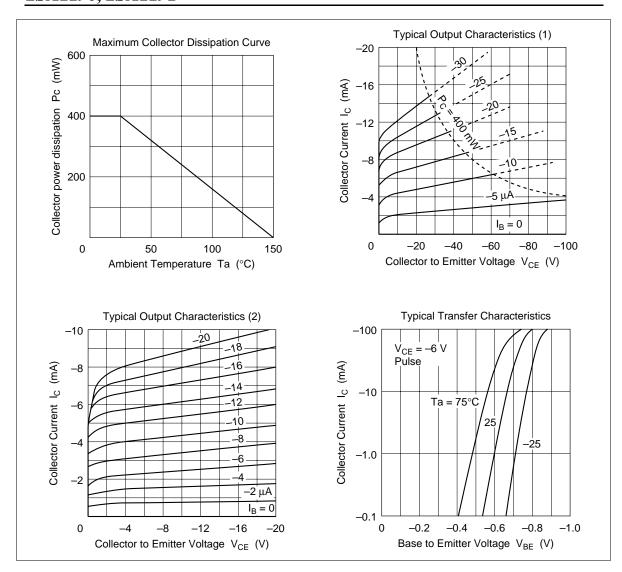
Electrical Characteristics ($Ta = 25^{\circ}C$)

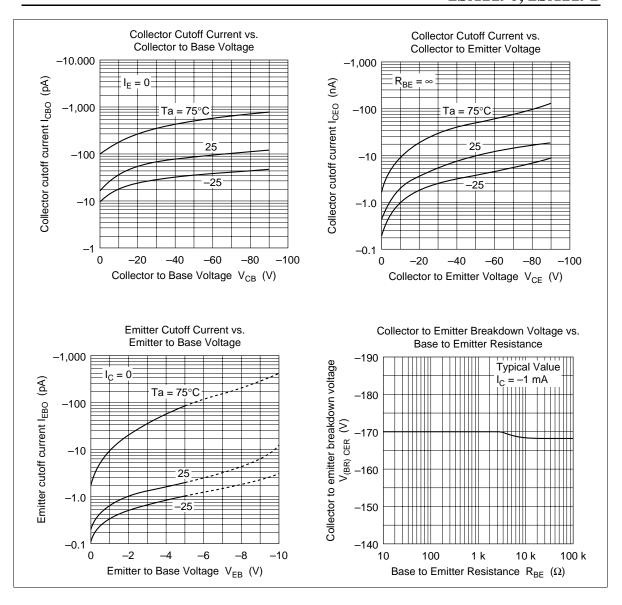
		2SA1190		2SA1191					
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-90	_	_	-120	_	_	V	$I_{c} = -10 \mu\text{A}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-90	_	_	-120	_	_	V	$I_{\rm C} = -1 \text{ mA}, R_{\rm BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	_	_	-5	_	_	V	$I_{E} = -10 \mu A, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	-0.1	_	_	-0.1	μΑ	$V_{CB} = -70 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	-0.1	_	_	-0.1	μΑ	$V_{EB} = -2 \text{ V}, I_{C} = 0$
DC current trnsfer ratio	h _{FE} *1	250	_	800	250	_	800		$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	-0.05	-0.15	_	-0.05	-0.15	V	$I_{\rm C} = -10 \text{ mA},$ $I_{\rm B} = -1 \text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{\text{BE(sat)}}$	_	-0.7	-1.0	_	-0.7	-1.0	V	
Gain bandwidth product	f _T	_	130	_	_	130	_	MHz	$V_{CE} = -6 \text{ V},$ $I_{C} = -10 \text{ mA}$
Collector output capacitance	Cob		3.2	_		3.2	_	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz
Noise figure	NF	_	0.15	1.5	_	0.15	1.5	dB	$V_{CE} = -6 \text{ V},$ $I_{C} = -0.1 \text{ mA},$ $R_{g} = 10 \text{ k}\Omega$ $f = 1 \text{ kHz}$
		_	0.2	2.0	_	0.2	2.0	dB	$V_{CE} = -6 \text{ V},$ $I_{C} = -0.1 \text{ mA},$ $R_{g} = 10 \text{ k}\Omega$ $f = 10 \text{ Hz}$
Noise voltage reffered to input	e _n		0.7	_		0.7	_	nV/ √Hz	$V_{CB} = -6 \text{ V},$ $I_{C} = -10 \text{ mA},$ $Rg = 0, f = 1 \text{ kHz}$

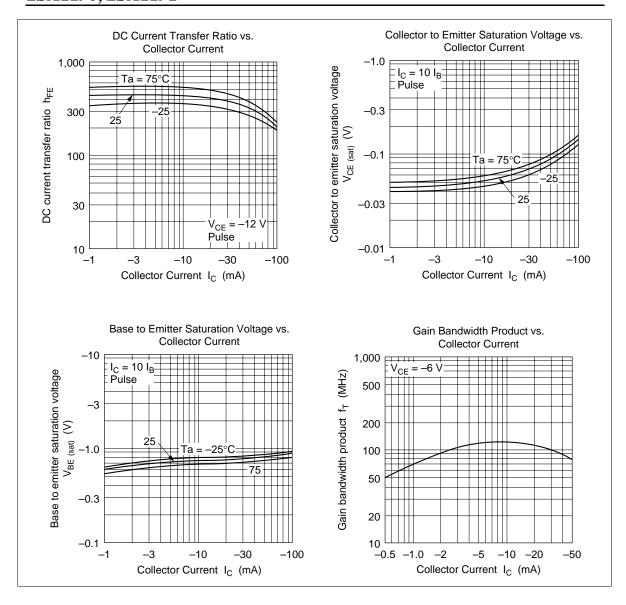
Notes: 1. The 2SA1190 and 2SA1191 are grouped by h_{FE} as follows.

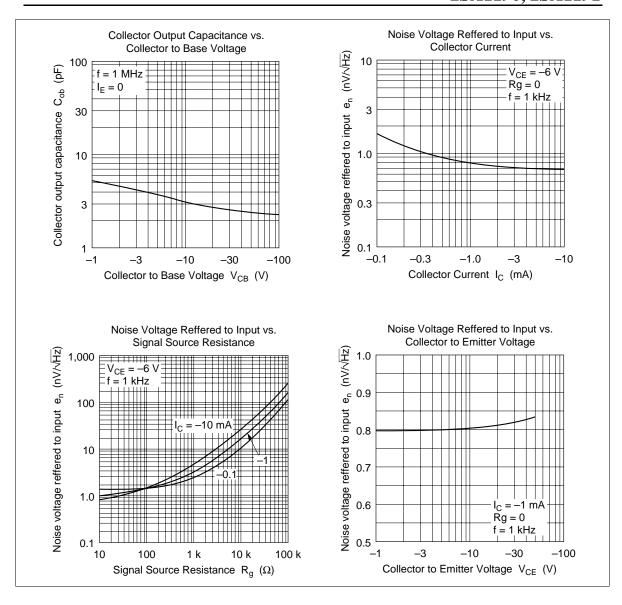
2. Pulse test

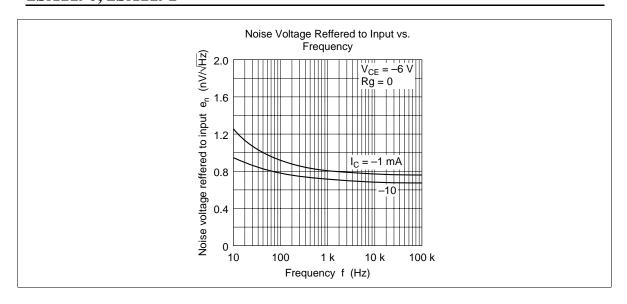
D E 250 to 500 400 to 800



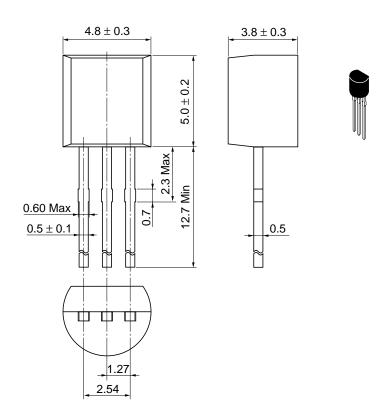








Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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